

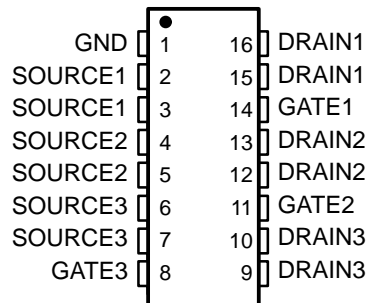
TPIC5302

3-CHANNEL INDEPENDENT POWER DMOS ARRAY

SLIS029B – APRIL 1994 – REVISED SEPTEMBER 1995

- Low $r_{DS(on)}$. . . 0.3 Ω Typ
- High-Voltage Outputs . . . 60 V
- Pulsed Current . . . 7 A Per Channel
- Fast Commutation Speed

**D PACKAGE
(TOP VIEW)**

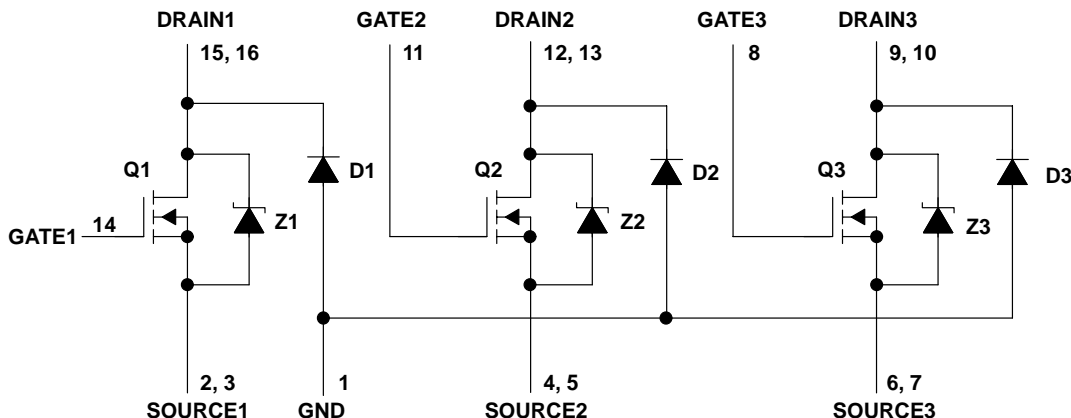


description

The TPIC5302 is a monolithic power DMOS array that consists of three electrically isolated independent N-channel enhancement-mode DMOS transistors. The TPIC5302 is offered in a standard 16-pin small-outline surface-mount (D) package.

The TPIC5302 is characterized for operation over the case temperature range of -40°C to 125°C .

schematic



absolute maximum ratings over operating case temperature range (unless otherwise noted)†

Drain-to-source voltage, V_{DS}	60 V
Source-to-GND voltage	100 V
Drain-to-GND voltage	100 V
Gate-to-source voltage, V_{GS}	± 20 V
Continuous drain current, each output, all outputs on, $T_C = 25^{\circ}\text{C}$	1.4 A
Continuous source-to-drain diode current	1.4 A
Pulsed drain current, each output, $T_C = 25^{\circ}\text{C}$ (see Note 1 and Figure 6)	7 A
Single-pulse avalanche energy, E_{AS} , $T_C = 25^{\circ}\text{C}$ (see Figure 4)	10.5 mJ
Continuous total power dissipation at (or below) $T_C = 25^{\circ}\text{C}$	1087 mW
Operating virtual junction temperature range, T_J	-40°C to 150°C
Operating case temperature range, T_C	-40°C to 125°C
Storage temperature range, T_{stg}	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: Pulse duration = 10 ms and duty cycle = 2%

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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electrical characteristics, $T_C = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$V_{(BR)DSX}$	Drain-to-source breakdown voltage	$I_D = 250\ \mu\text{A}$,	$V_{GS} = 0$	60			V
$V_{GS(th)}$	Gate-to-source threshold voltage	$I_D = 1\ \text{mA}$,	$V_{DS} = V_{GS}$	1.5	1.85	2.2	V
$V_{(BR)}$	Reverse drain-to-GND breakdown voltage (across D1, D2, and D3)	Drain-to-GND current = $250\ \mu\text{A}$		100			V
$V_{DS(on)}$	Drain-to-source on-state voltage	$I_D = 1.4\ \text{A}$, See Notes 2 and 3	$V_{GS} = 10\ \text{V}$,		0.42	0.49	V
$V_{F(SD)}$	Forward on-state voltage, source-to-drain	$I_S = 1.4\ \text{A}$, $V_{GS} = 0$ (Z1, Z2, Z3), See Notes 2 and 3			0.9	1.1	V
V_F	Forward on-state voltage, GND-to-drain	$I_D = 1.4\ \text{A}$			4.8		V
I_{DSS}	Zero-gate-voltage drain current	$V_{DS} = 48\ \text{V}$, $V_{GS} = 0$	$T_C = 25^\circ\text{C}$		0.05	1	μA
			$T_C = 125^\circ\text{C}$		0.5	10	
I_{GSSF}	Forward gate current, drain short circuited to source	$V_{GS} = 16\ \text{V}$,	$V_{DS} = 0$		10	100	nA
I_{GSSR}	Reverse gate current, drain short circuited to source	$V_{SG} = 16\ \text{V}$,	$V_{DS} = 0$		10	100	nA
I_{lkg}	Leakage current, drain-to-GND	$V_R = 48\ \text{V}$	$T_C = 25^\circ\text{C}$		0.05	1	μA
			$T_C = 125^\circ\text{C}$		0.5	10	
$r_{DS(on)}$	Static drain-to-source on-state resistance	$V_{GS} = 10\ \text{V}$, $I_D = 1.4\ \text{A}$, See Notes 2 and 3 and Figures 6 and 7	$T_C = 25^\circ\text{C}$		0.3	0.35	Ω
			$T_C = 125^\circ\text{C}$		0.41	0.5	
g_{fs}	Forward transconductance	$V_{DS} = 10\ \text{V}$, See Notes 2 and 3	$I_D = 0.7\ \text{A}$,	1.15	1.41		S
C_{iss}	Short-circuit input capacitance, common source	$V_{DS} = 25\ \text{V}$, $f = 1\ \text{MHz}$	$V_{GS} = 0$,		135	170	pF
C_{oss}	Short-circuit output capacitance, common source				80	100	
C_{rss}	Short-circuit reverse-transfer capacitance, common source				30	40	

- NOTES: 2. Technique should limit $T_J - T_C$ to 10°C maximum and pulse duration $\leq 5\ \text{ms}$.
3. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

source-to-drain diode characteristics, $T_C = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$t_{rr(SD)}$	Reverse-recovery time	$I_S = 0.5\ \text{A}$,	$V_{GS} = 0$, $V_{DS} = 48\ \text{V}$, See Figure 1		35		ns
Q_{RR}	Total diode charge	$di/dt = 100\ \text{A}/\mu\text{s}$,			0.04		μC

GND-to-drain diode characteristics, $T_C = 25^\circ\text{C}$ (see schematic, D1, D2, and D3)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{rr}	Reverse-recovery time	$I_F = 0.5\ \text{A}$,	$V_{DS} = 48\ \text{V}$, See Figure 1		130		ns
Q_{RR}	Total diode charge	$di/dt = 100\ \text{A}/\mu\text{s}$,			0.4		μC



resistive-load switching characteristics, $T_C = 25^\circ\text{C}$

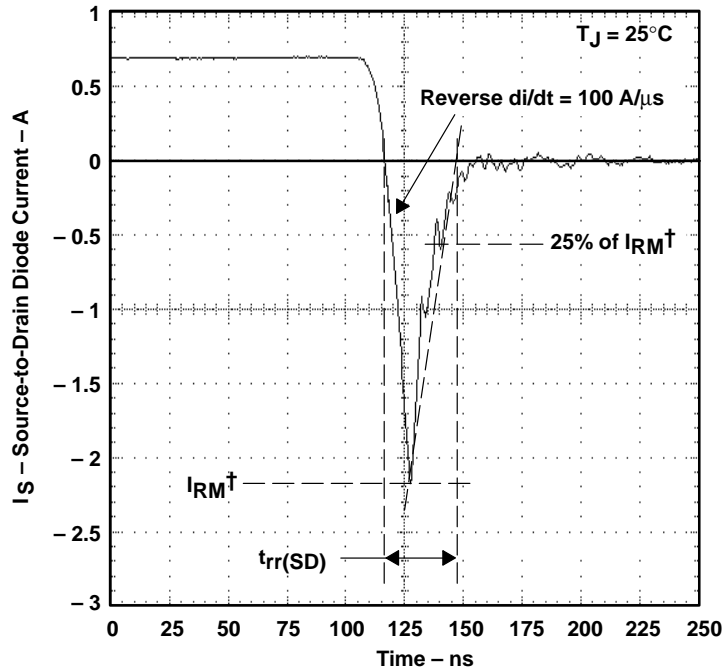
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{d(on)}$ Turn-on delay time	$V_{DD} = 25\text{ V}, R_L = 50\ \Omega, t_{r1} = 10\text{ ns},$ $t_{f1} = 10\text{ ns},$ See Figure 2		23	46	ns
$t_{d(off)}$ Turn-off delay time			25	50	
t_{r2} Rise time			5	10	
t_{f2} Fall time			17	34	
Q_g Total gate charge	$V_{DS} = 48\text{ V}, I_D = 0.5\text{ A}, V_{GS} = 10\text{ V},$ See Figure 3		8	9.8	nC
$Q_{gs(th)}$ Threshold gate-to-source charge			0.5	0.63	
Q_{gd} Gate-to-drain charge			1.5	1.85	
L_D Internal drain inductance			5		nH
L_S Internal source inductance			5		
R_g Internal gate resistance			0.25		Ω

thermal resistance

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JA}$ Junction-to-ambient thermal resistance	All outputs with equal power, See Note 4		115		$^\circ\text{C}/\text{W}$
$R_{\theta JP}$ Junction-to-pin thermal resistance			32		

NOTE 4: Package mounted on an FR4 printed-circuit board with no heat sink

PARAMETER MEASUREMENT INFORMATION



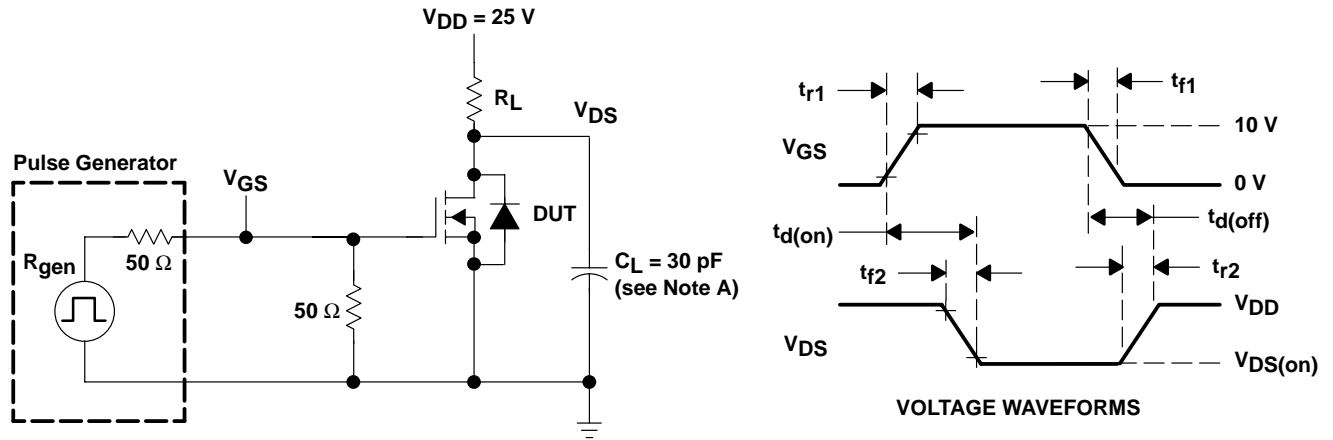
$^\dagger I_{RM}$ = maximum recovery current

Figure 1. Reverse-Recovery-Current Waveform of Source-to-Drain Diode

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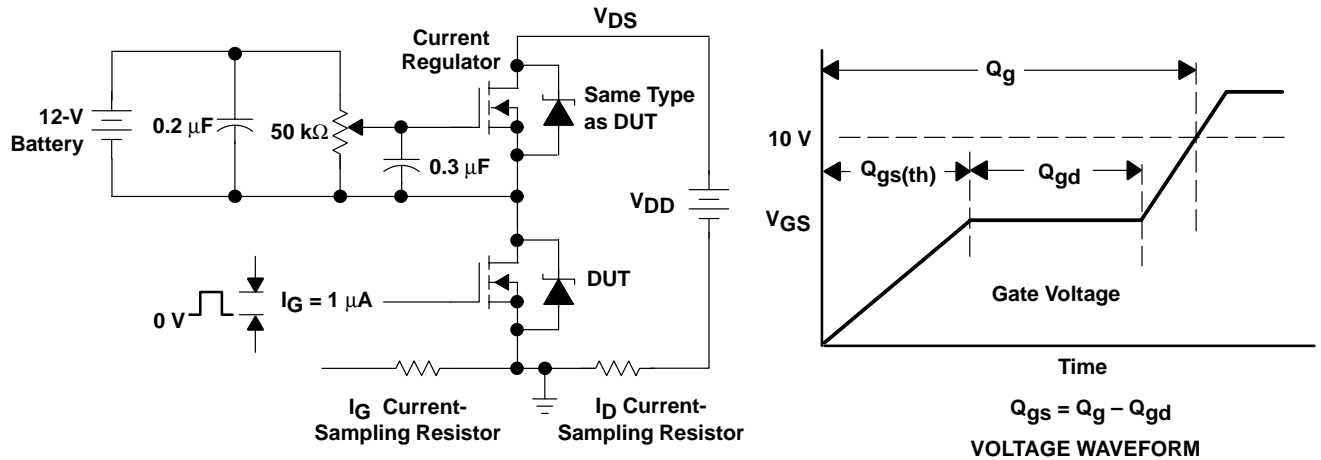
PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

NOTE A: C_L includes probe and jig capacitance.

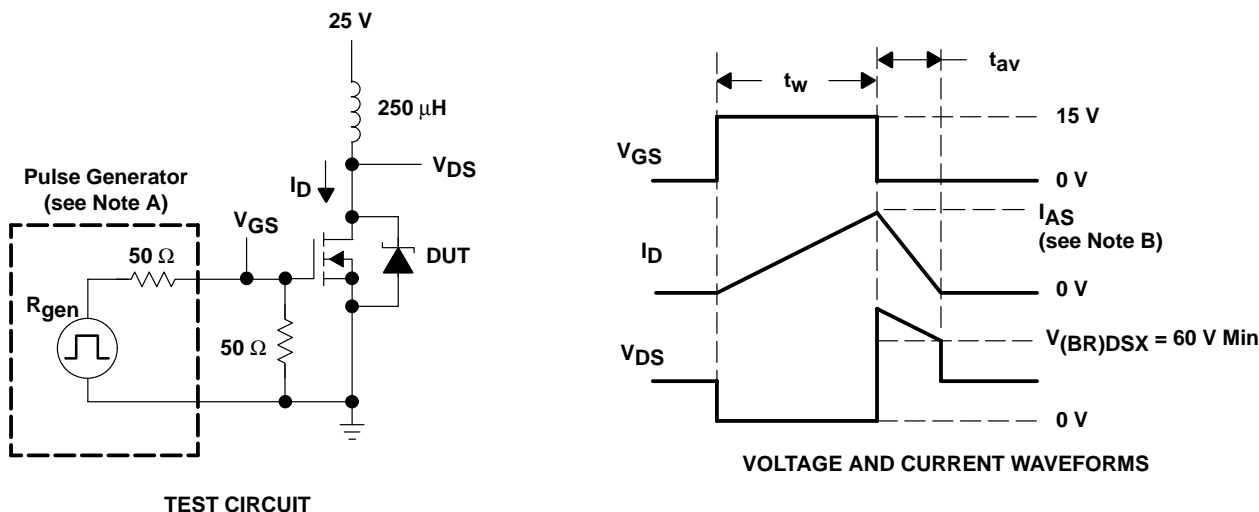
Figure 2. Resistive-Switching Test Circuit and Voltage Waveforms



TEST CIRCUIT

Figure 3. Gate-Charge Test Circuit and Voltage Waveform

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The pulse generator has the following characteristics: $t_r \leq 10$ ns, $t_f \leq 10$ ns, $Z_O = 50 \Omega$.
B. Input pulse duration (t_w) is increased until peak current $I_{AS} = 7$ A, where t_{av} = avalanche time.

$$\text{Energy test level is defined as } E_{AS} = \frac{I_{AS} \times V_{(BR)DSX} \times t_{av}}{2} = 10.5 \text{ mJ}$$

Figure 4. Single-Pulse Avalanche-Energy Test Circuit and Waveforms

TYPICAL CHARACTERISTICS

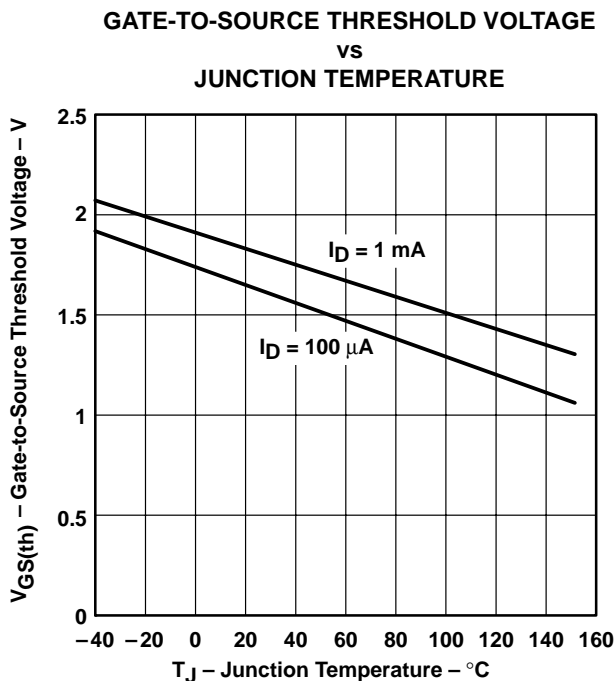


Figure 5

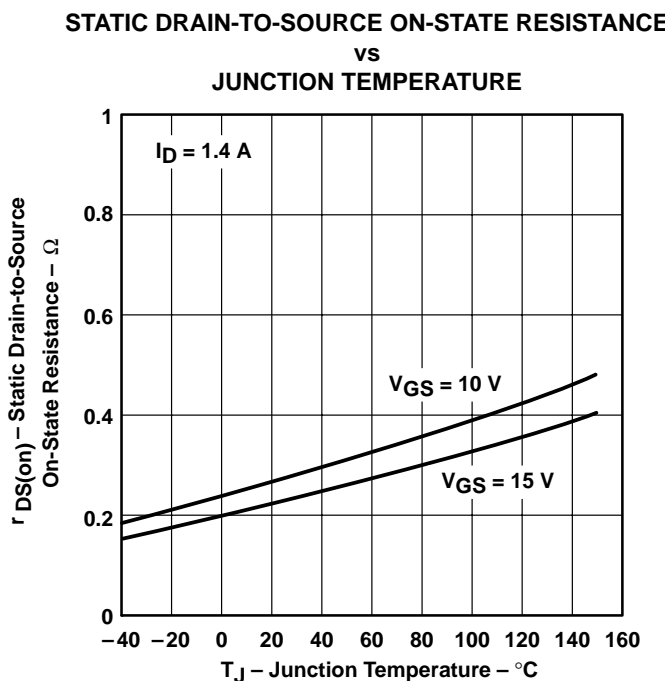


Figure 6

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TYPICAL CHARACTERISTICS

STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE
vs
DRAIN CURRENT

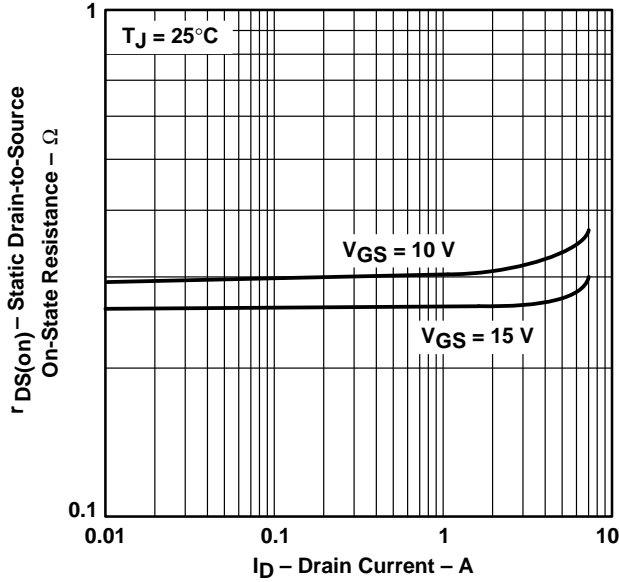


Figure 7

DRAIN CURRENT
vs
DRAIN-TO-SOURCE VOLTAGE

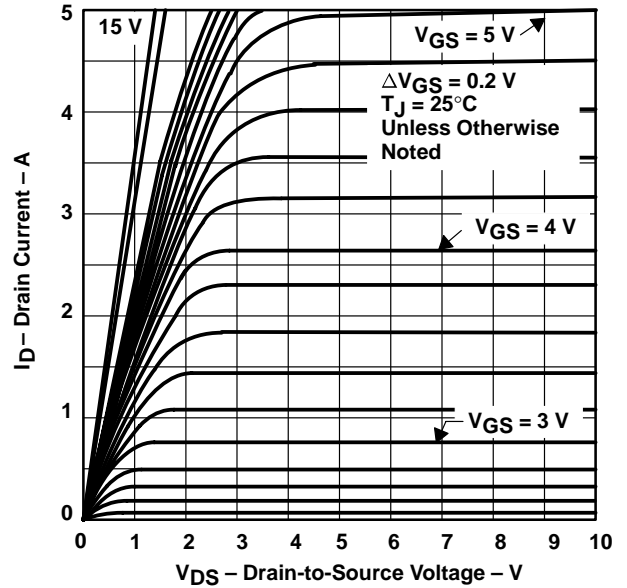


Figure 8

DISTRIBUTION OF
FORWARD TRANSCONDUCTANCE

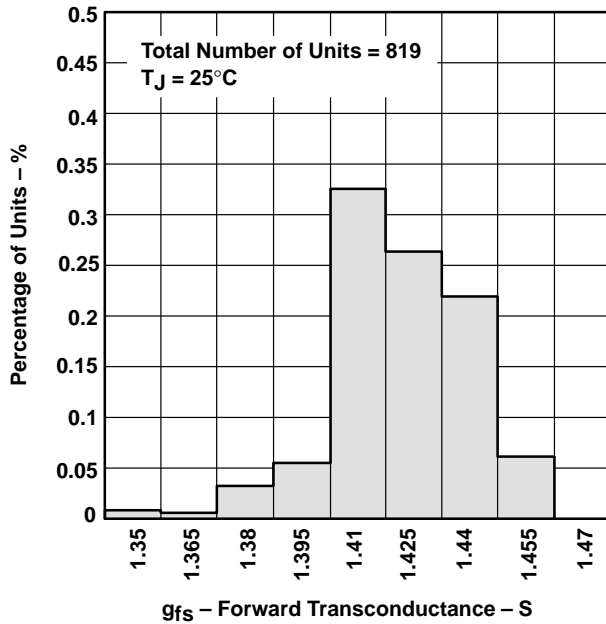


Figure 9

DRAIN CURRENT
vs
GATE-TO-SOURCE VOLTAGE

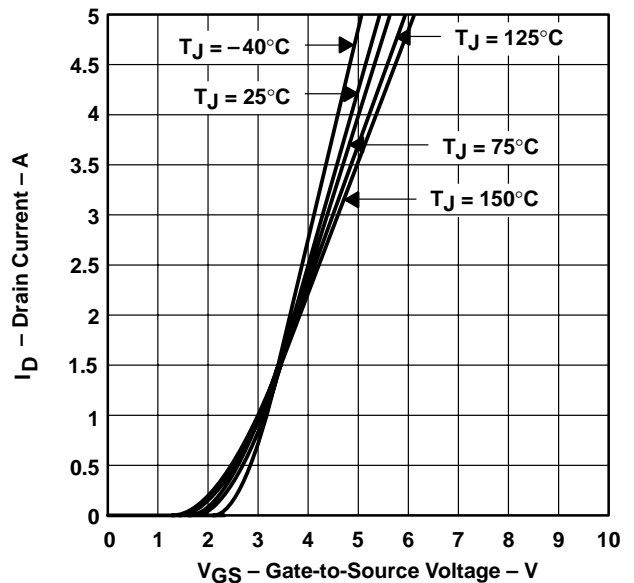
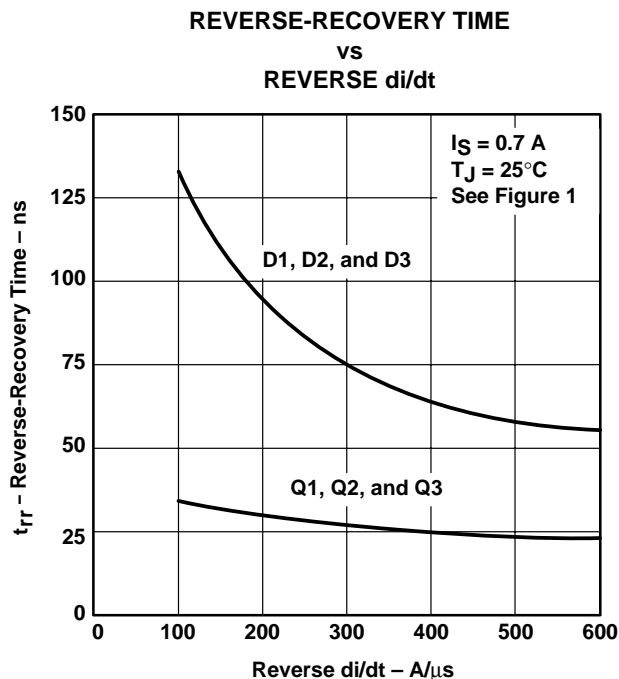
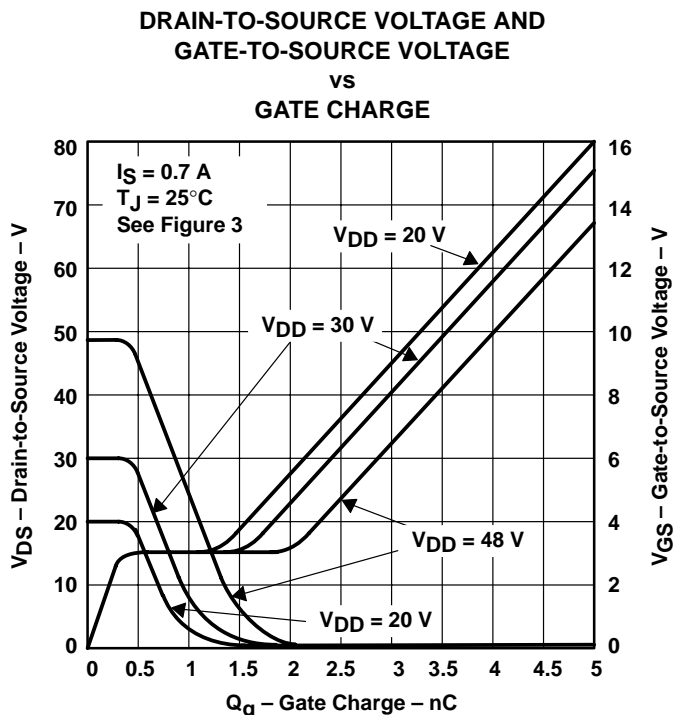
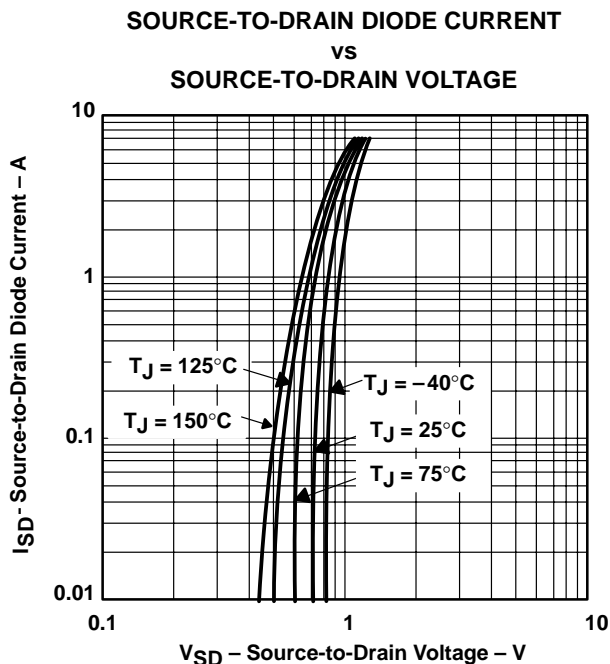
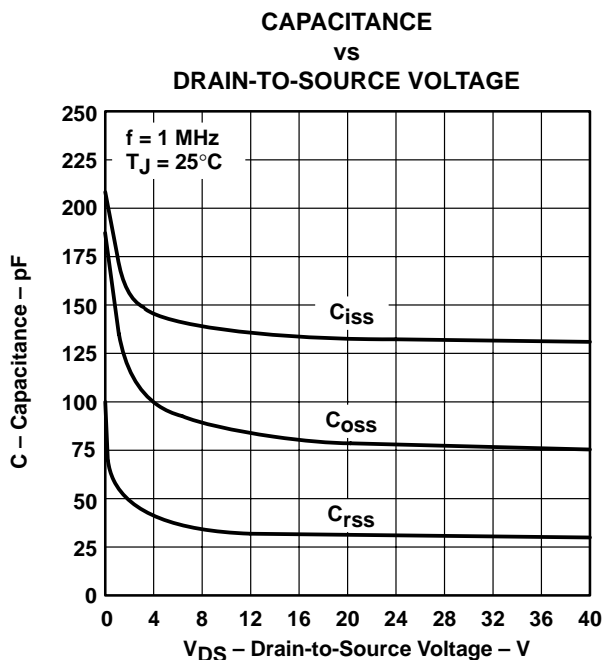


Figure 10



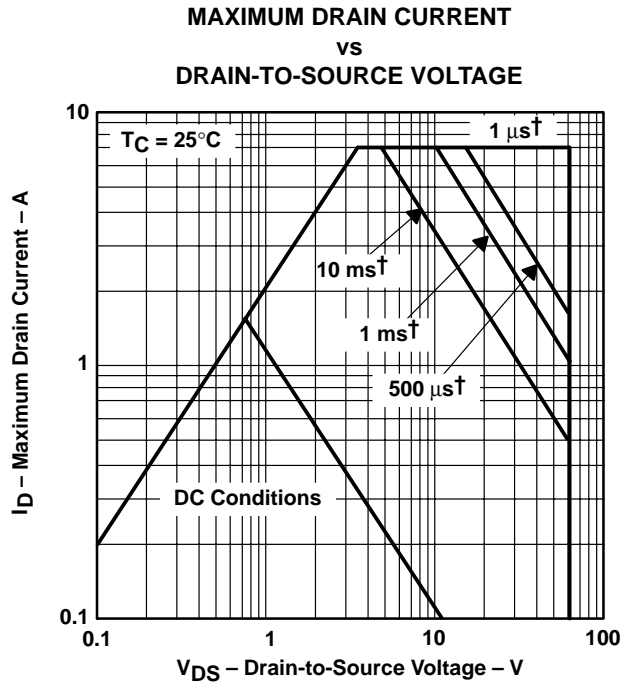
TYPICAL CHARACTERISTICS



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THERMAL INFORMATION



† Less than 0.1 duty cycle

Figure 15

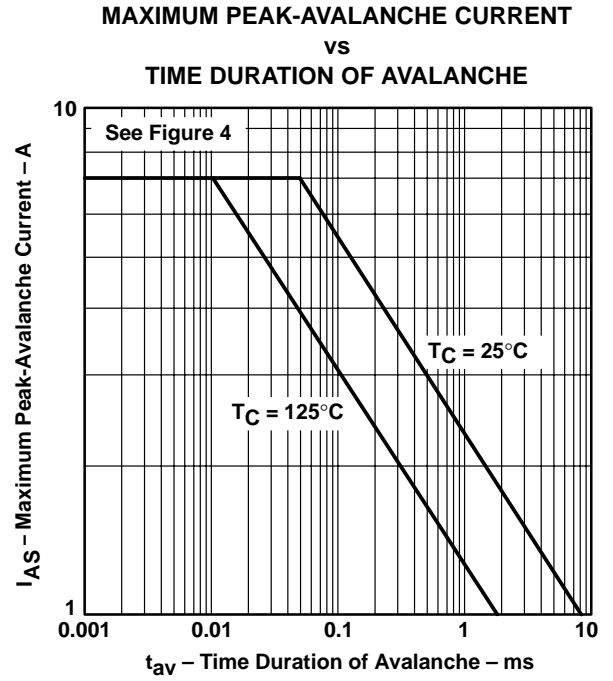
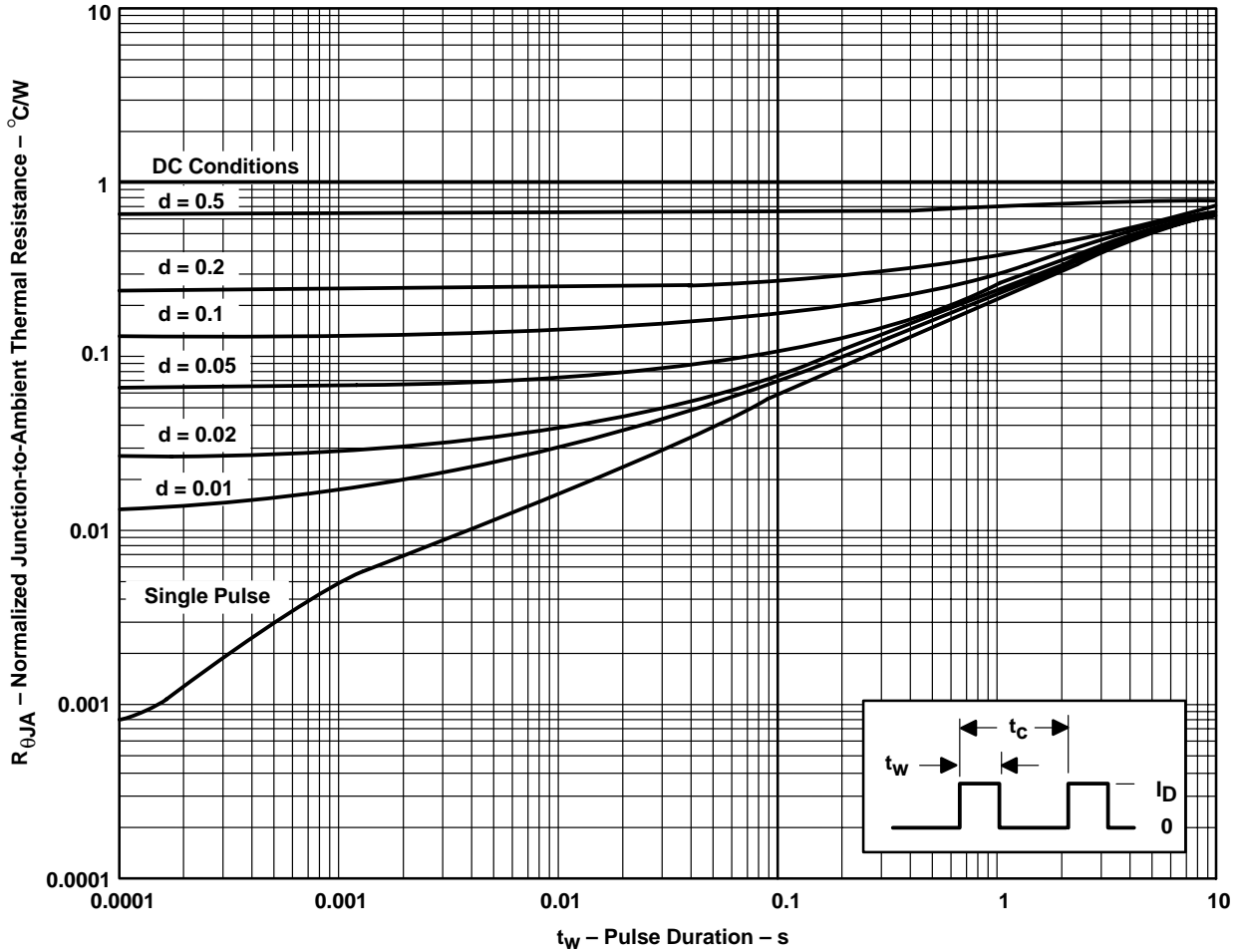


Figure 16

THERMAL INFORMATION

D PACKAGE†
 NORMALIZED JUNCTION-TO-AMBIENT THERMAL RESISTANCE
 VS
 PULSE DURATION



† Device mounted on FR4 printed-circuit board with no heat sink

NOTE A: $Z_{\theta A}(t) = r(t) R_{\theta JA}$
 t_w = pulse duration
 t_c = cycle time
 d = duty cycle = t_w/t_c

Figure 17

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